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Halbleiterspeicheranordnung mit Fähigkeit zur Informationsverlusterkennung

Dispositif de mémoire à semi-conducteurs avec la capacité de détection de perte d'information

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(56) References cited:

**EP-A- 1 426 971 US-A- 5 359 205
US-A- 5 671 180 US-A- 5 999 448
US-A1- 2003 218 925 US-A1- 2004 165 456
US-B1- 6 249 841**

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